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## Silicon PNP Power Transistor

## 2SA1276

### DESCRIPTION

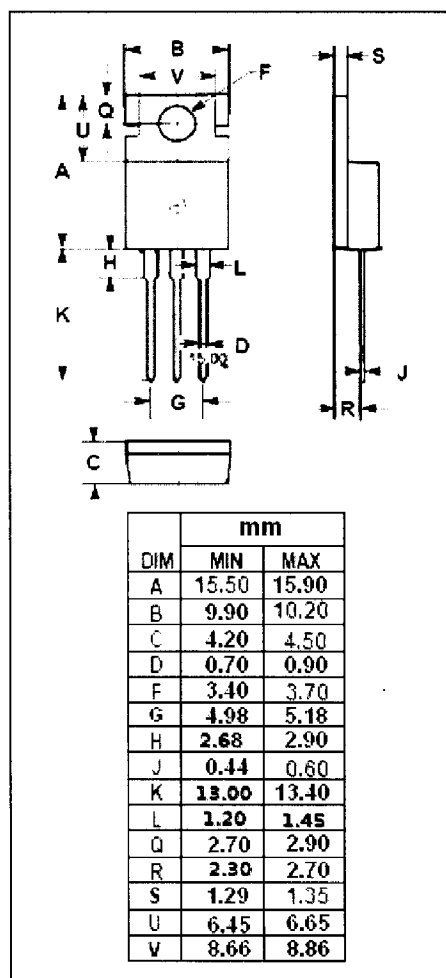
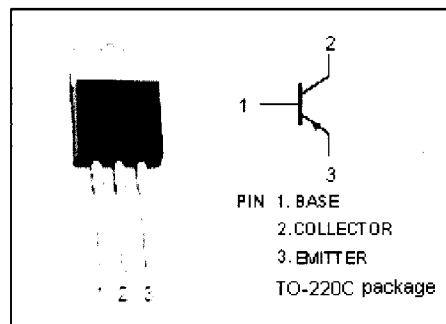
- Collector-Emitter Breakdown Voltage  
:  $V_{(BR)CEO} = -30V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SC3230

### APPLICATIONS

- Designed for general purpose applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-30	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-3	A
$I_E$	Emitter Current-Continuous	3	A
$P_C$	Total Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors**

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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-30			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$			-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -20\text{V}; I_E = 0$			-1.0	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-1.0	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$	70		240	
$h_{FE-2}$	DC Current Gain	$I_C = -2.5\text{A}; V_{CE} = -2\text{V}$	25			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$		100		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1.0\text{MHz}$		40		pF

◆  $h_{FE-1}$  Classifications

O	Y
70-140	120-240